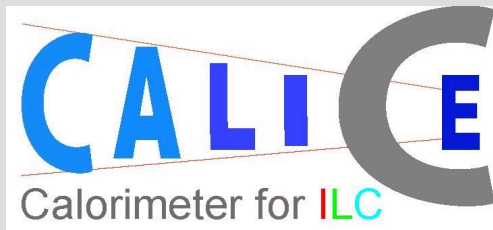


Simulation of Monolithic Active Pixel Sensors for ILC ECAL

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Outline

- **Introduction**
- **MAPS (Monolithic Active Pixel Sensors)**
 - Concepts
 - Design
- **Geometry modification**
- **Single e-/ μ - simulation**
 - Si sensitive thickness dependence
 - Cell size dependence
 - Incoming energy dependence
- **Summary of status**
- **Future prospects**

Introduction

- **High granularity**
 - Small cells
 - **Digital Calorimetry**
- **Cost saving**
 - Using CMOS silicon
 - **Cheaper than high resistance pure silicon**
 - Si thickness reduction
 - **Reduction of outer sub-detector volume**

MAPS concepts

- **Detecting individual particles after electromagnetic cascade shower by small cells**
- Result in measuring a single particle in a cell
 - Binary readout
 - Digital calorimetry
 - ➔ **High granularity**

MAPS design

- Analogue design
 - 1cm X 1cm cell
 - 500 μ m Si sensitive thickness
 - 500 μ m Si physical thickness
 - Analogue readout
- MAPS design
 - 50 μ m X 50 μ m cell
 - ~15 μ m Si sensitive thickness
 - 300 μ m Si physical thickness
 - Binary readout
 - One PCB per layer

W thickness is the same with both cases.

Geometry modification

Default

Upper PCB	800 μ m
Si Sensitive	500 μ m
Lower PCB	800 μ m

MAPS (test)

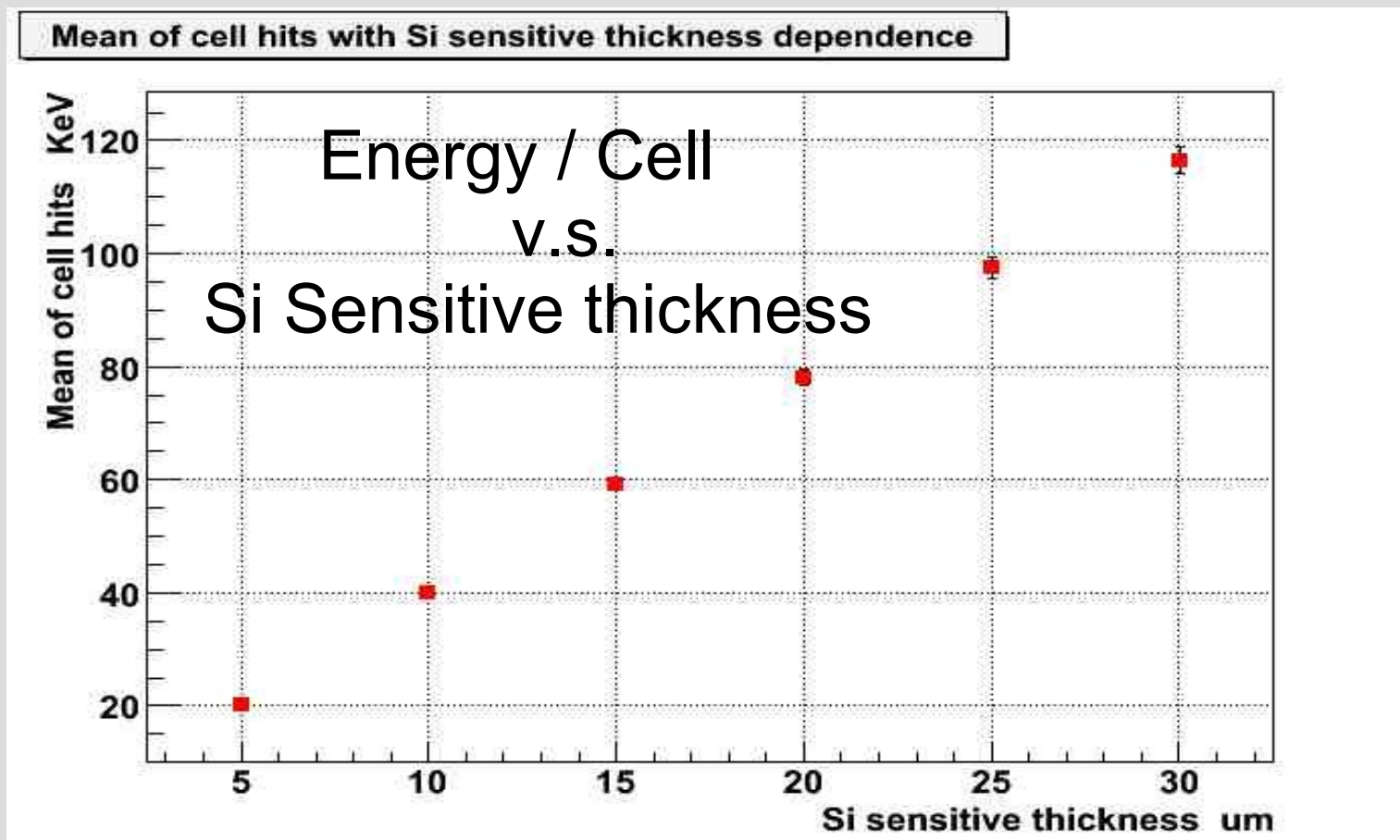
Upper PCB	800 μ m
Si Sensitive	15 μ m
Si Non-sensitive	485 μ m
Lower PCB	800 μ m

- Mokka 06-00
- Ecal02.cc (Geant4 ECAL driver) is modified.
- Geant4 Adaptive GUI output is fine.
- Energy deposit agreed with the expect.
(i.e. $15\mu\text{m}/500\mu\text{m} = 3.0\%$)
- Layer position shift agreed with the expect.

Single e- simulation (1.a)

(Si sensitive thickness dependence)

20 GeV single electron (from IP to zenith with magnet on)
Cell size is 1cm X 1cm

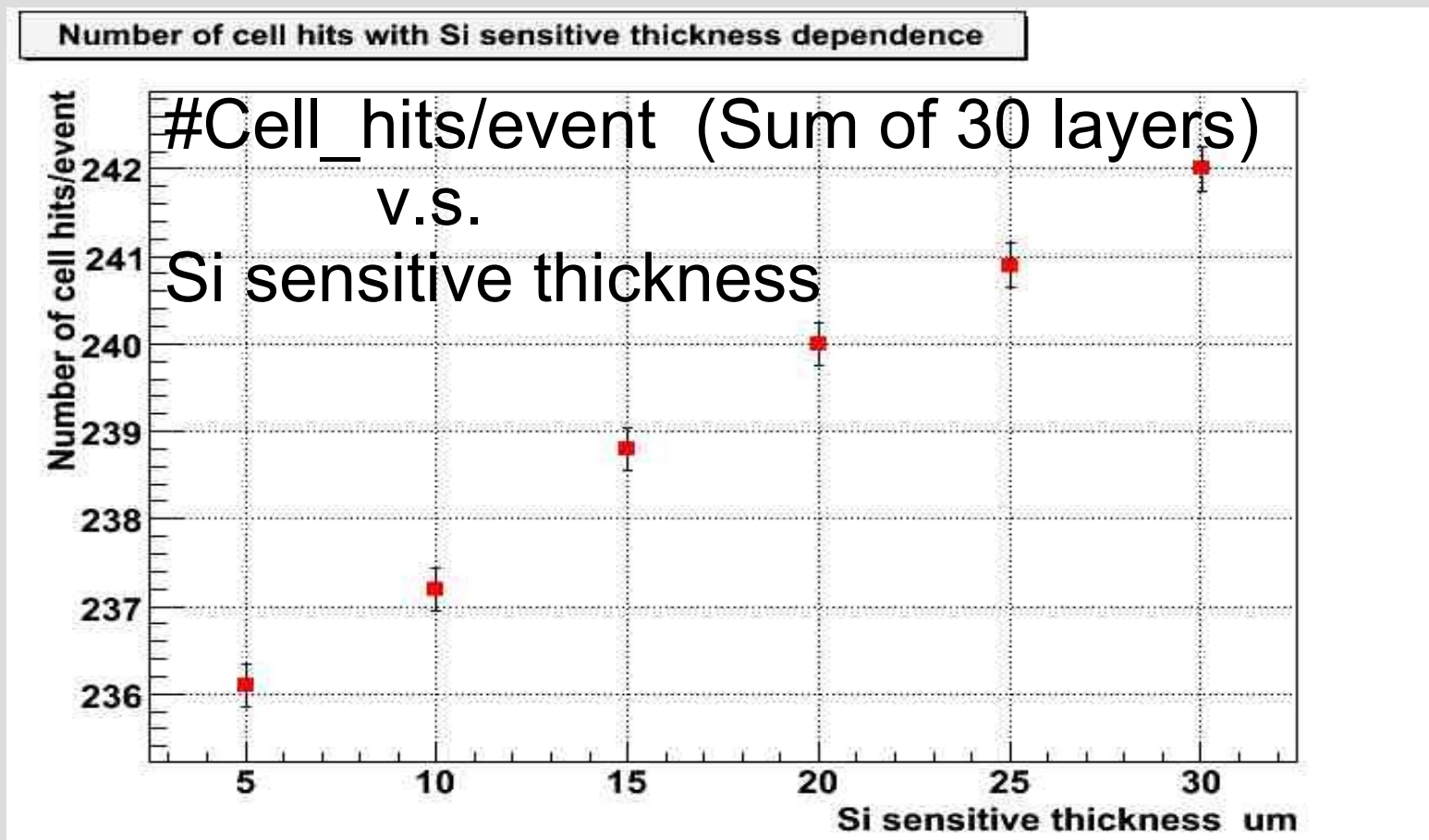


No threshold is applied for energy of cell hits

Single e- simulation (1.b)

(Si sensitive thickness dependence)

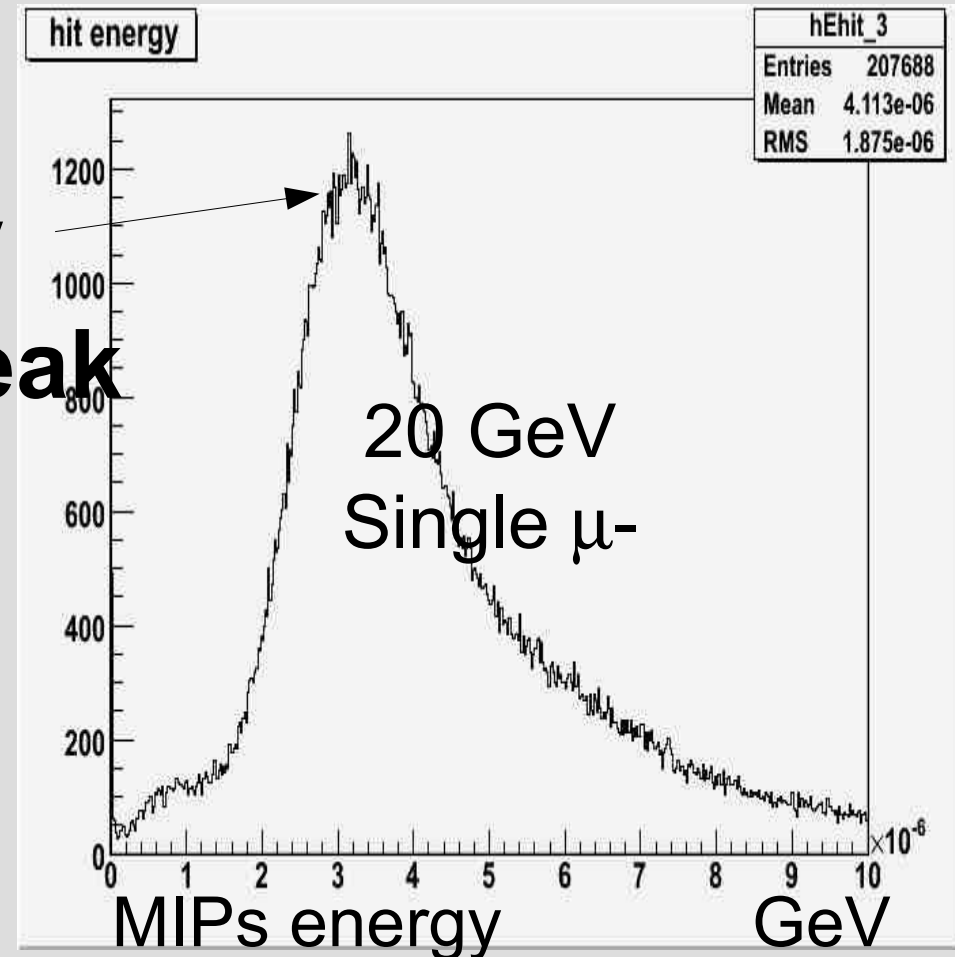
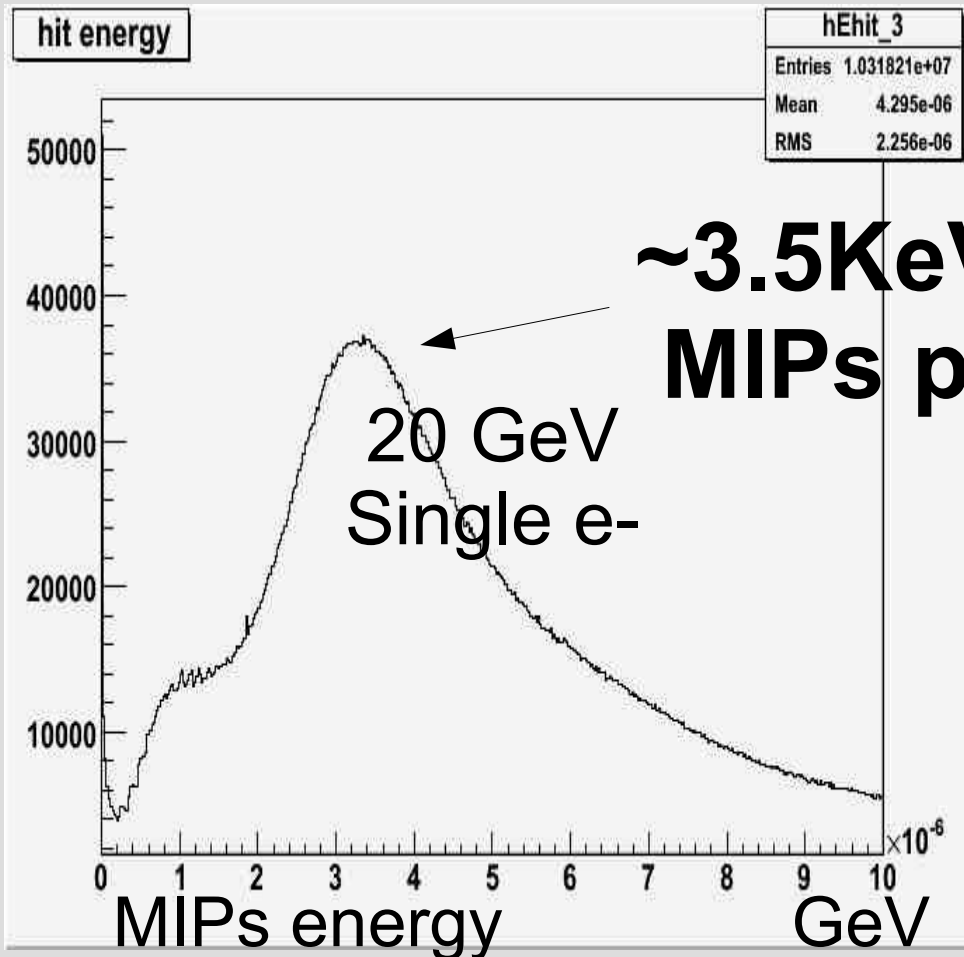
20 GeV single electron
Cell size is 1cm X 1cm



Only a few % dependence

Single e-/μ- simulation (2)

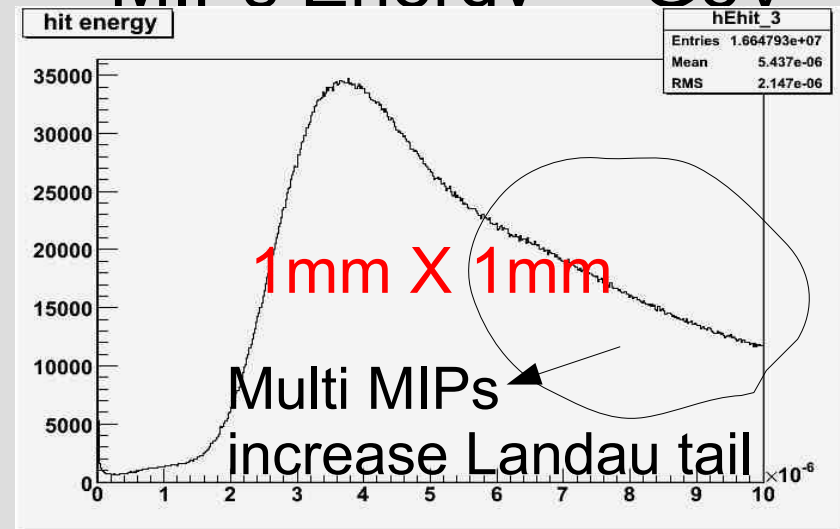
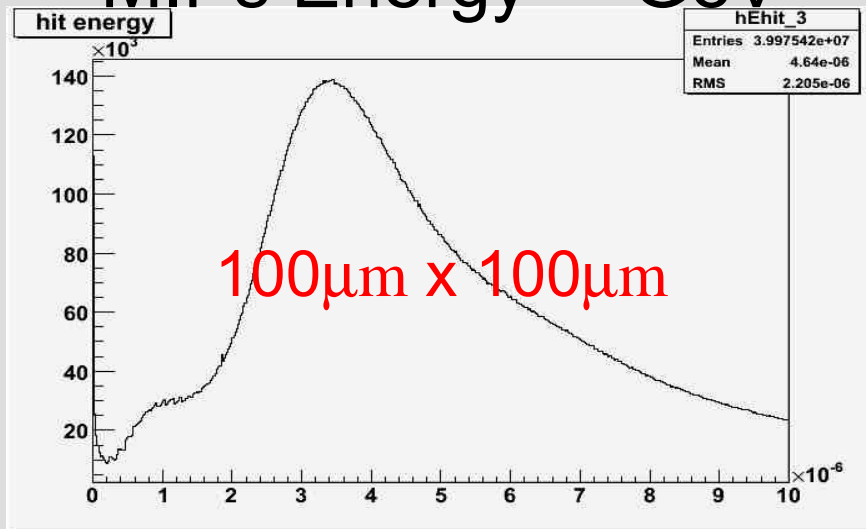
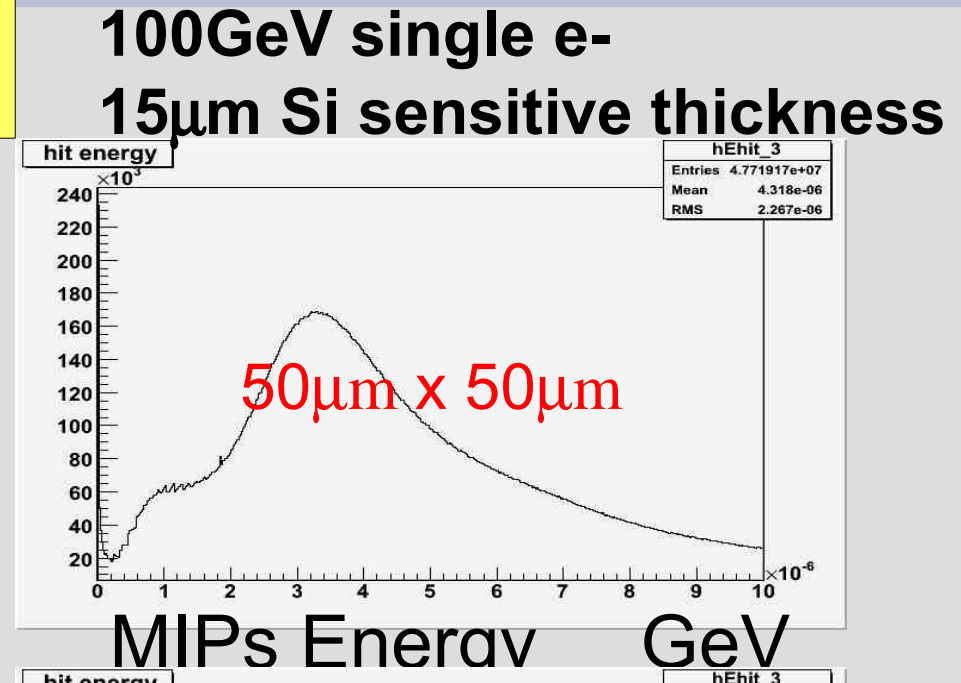
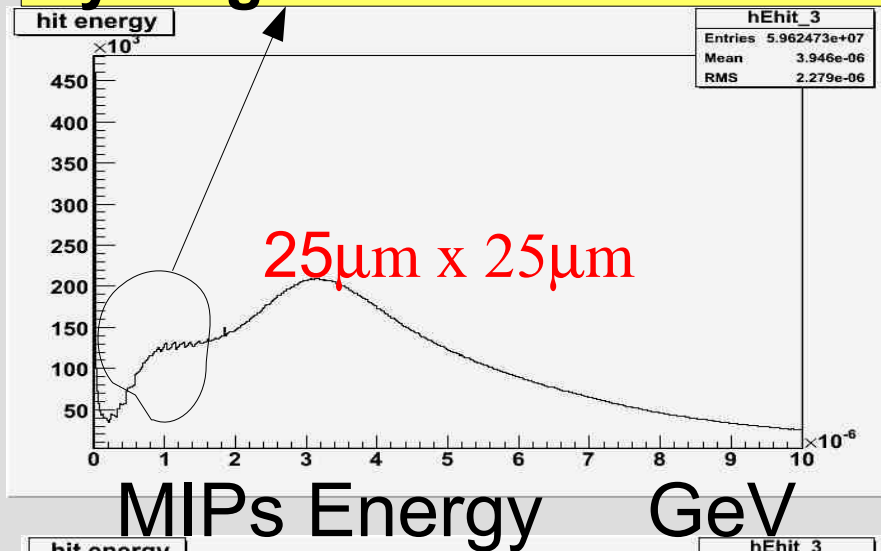
15μm Si sensitive thickness
50μm X 50μm cell size



Single e- simulation (3.a)

(Cell size dependence)

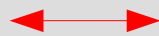
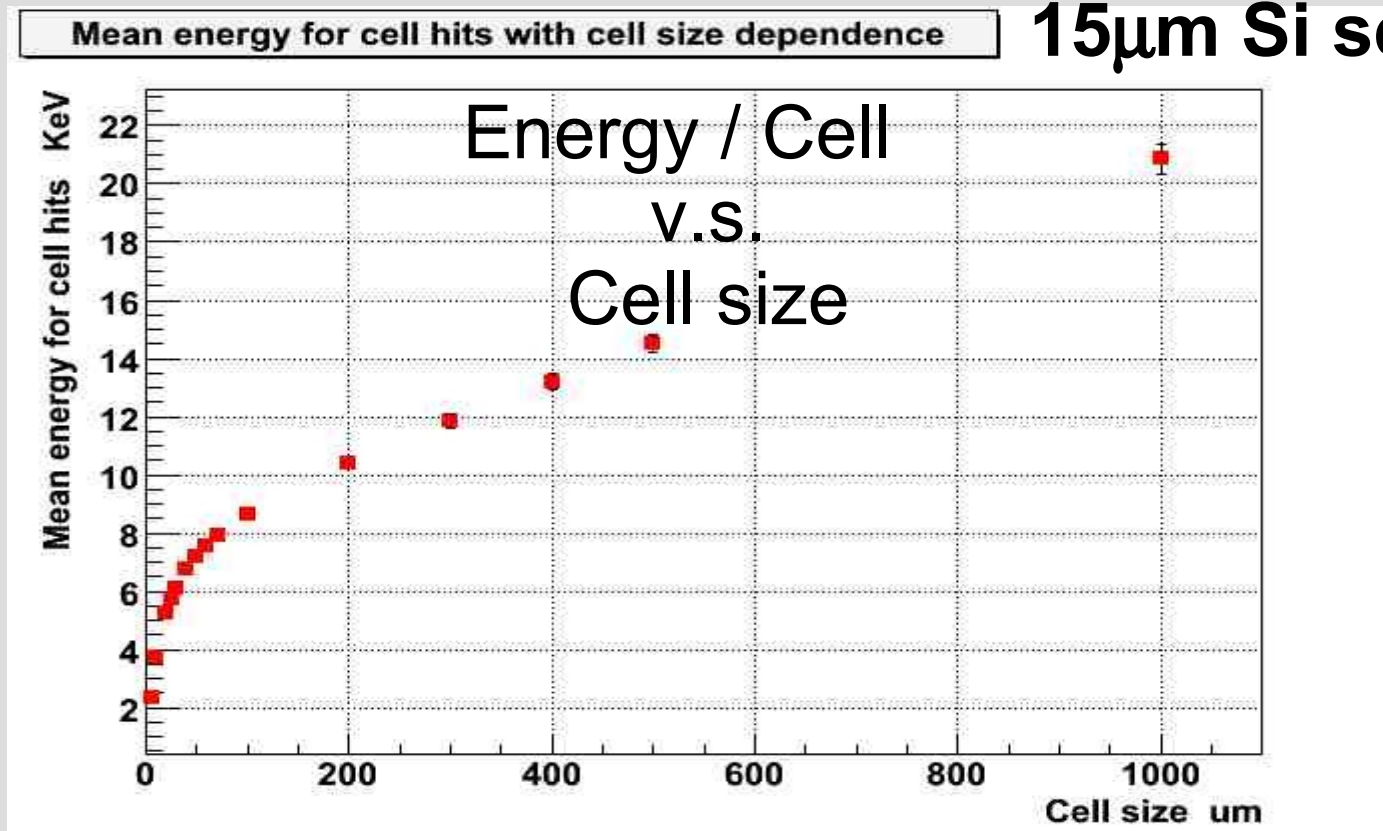
Energy of one MIP is sharing by neighbour cell at boundary.



Single e- simulation (3.b)

(Cell size dependence)

100GeV e-
15 μ m Si sensitive

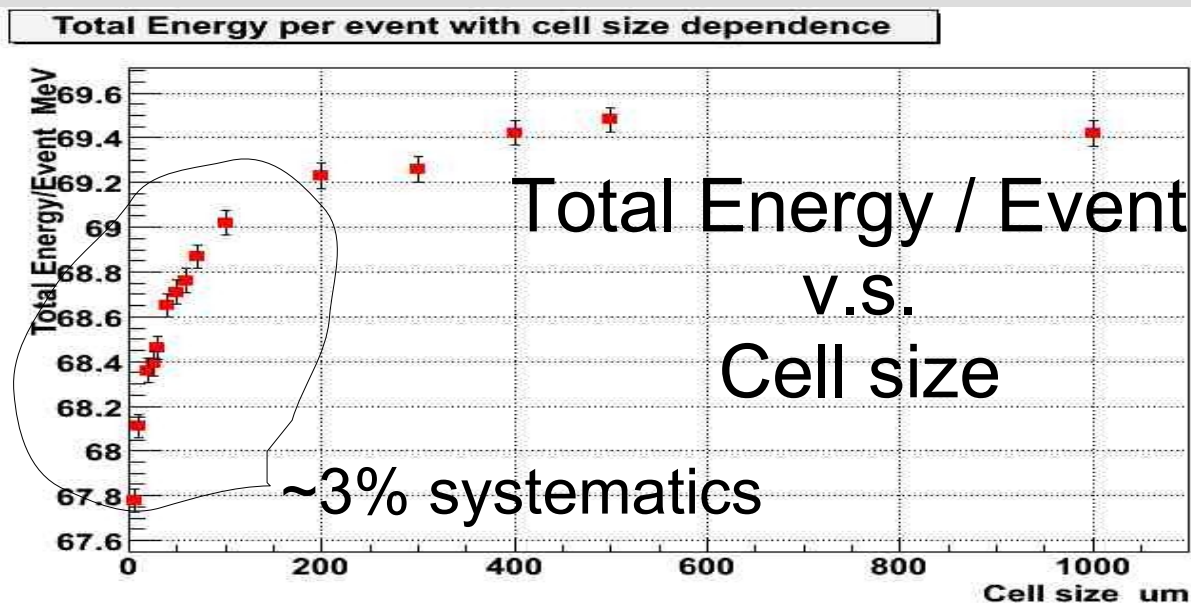
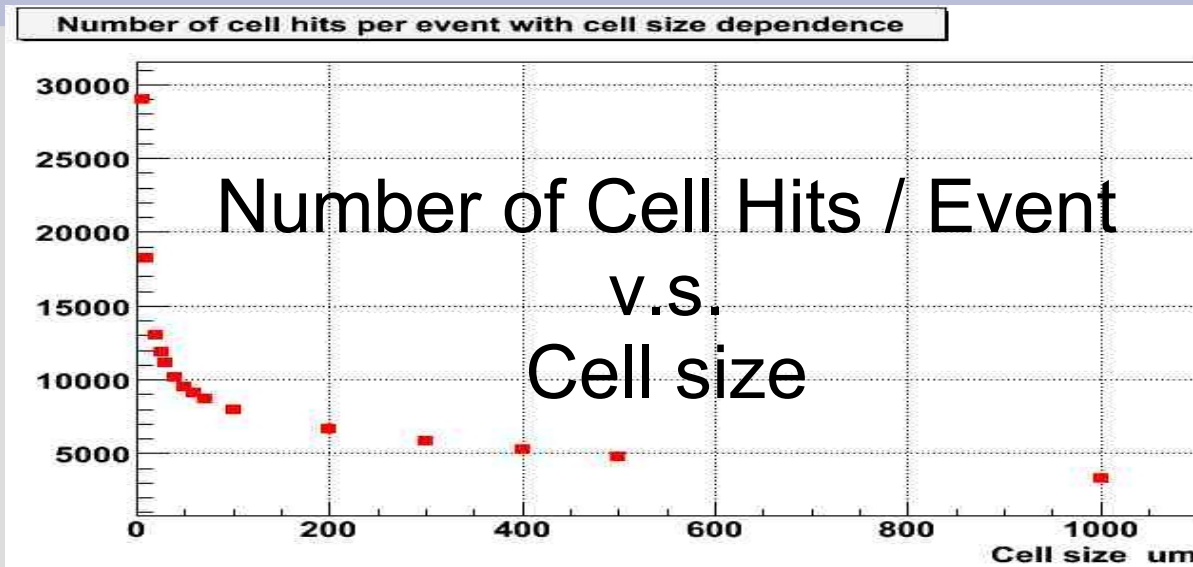


- One MIP per cell
- One MIP's energy deposit is sharing by neighbour cell

Single e- simulation (3.c)

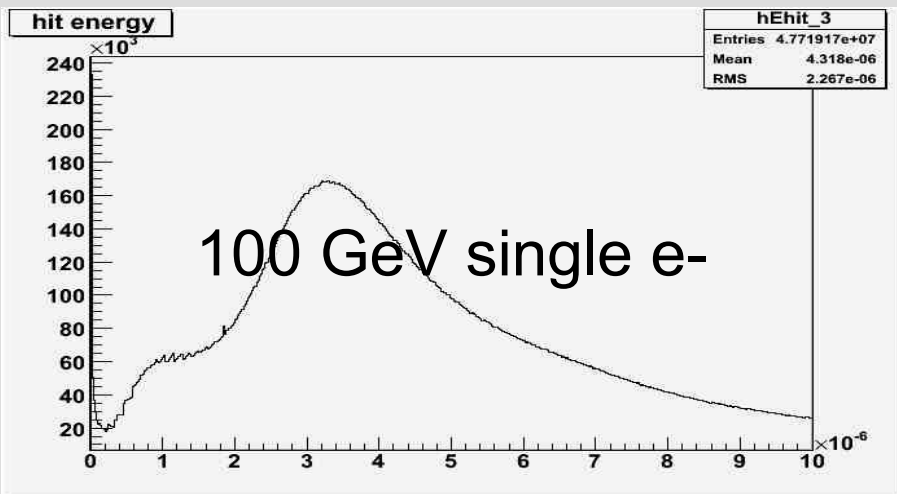
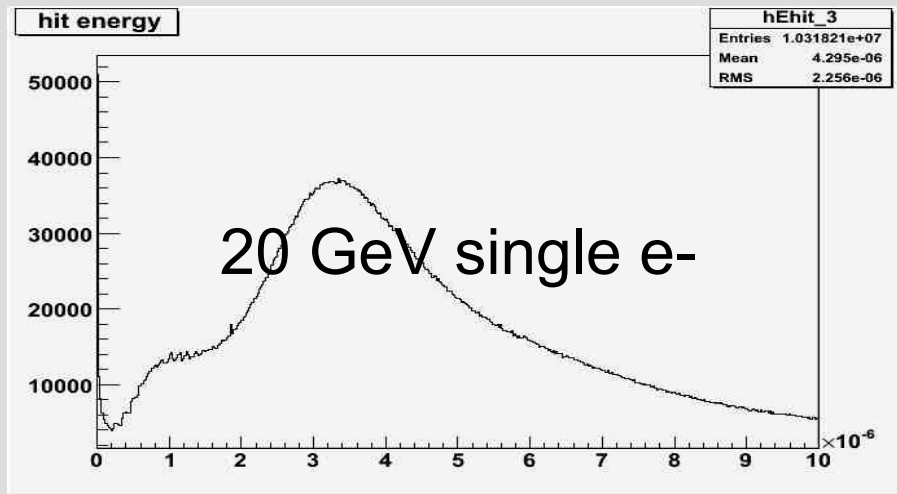
(Cell size dependence: consistency checks)

100GeV e-
15 μ m Si sensitive

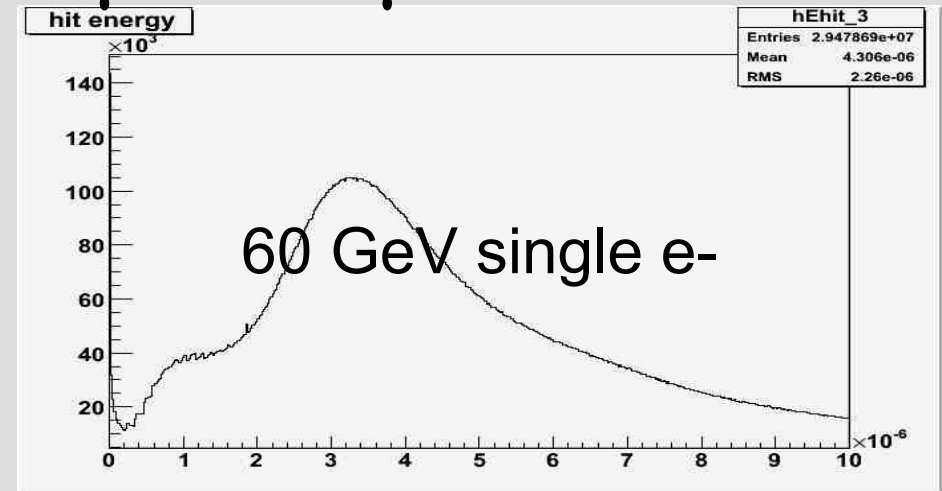


Single e- simulation (4)

(Incoming energy dependence)



15 μm Si sensitive thickness
50 μm X 50 μm cell size



Mean of peak is independent
of incoming energy.

→ **One MIP per cell**

→ Digital calorimetry

Cell hit number is proportional to incoming energy.

Summary of status

- **MAPS test geometry is implemented.**
- **Each cell has only one MIP in most case.**
- **Charge sharing by neighbour cell is seen.**
- **50 μ m X 50 μ m cell seems to be reasonable.**
- **Sensor level simulation is ongoing as well.**
(Giulio Villani et al. -> please see Konstantin Stefanov's talk at calorimetry session.)

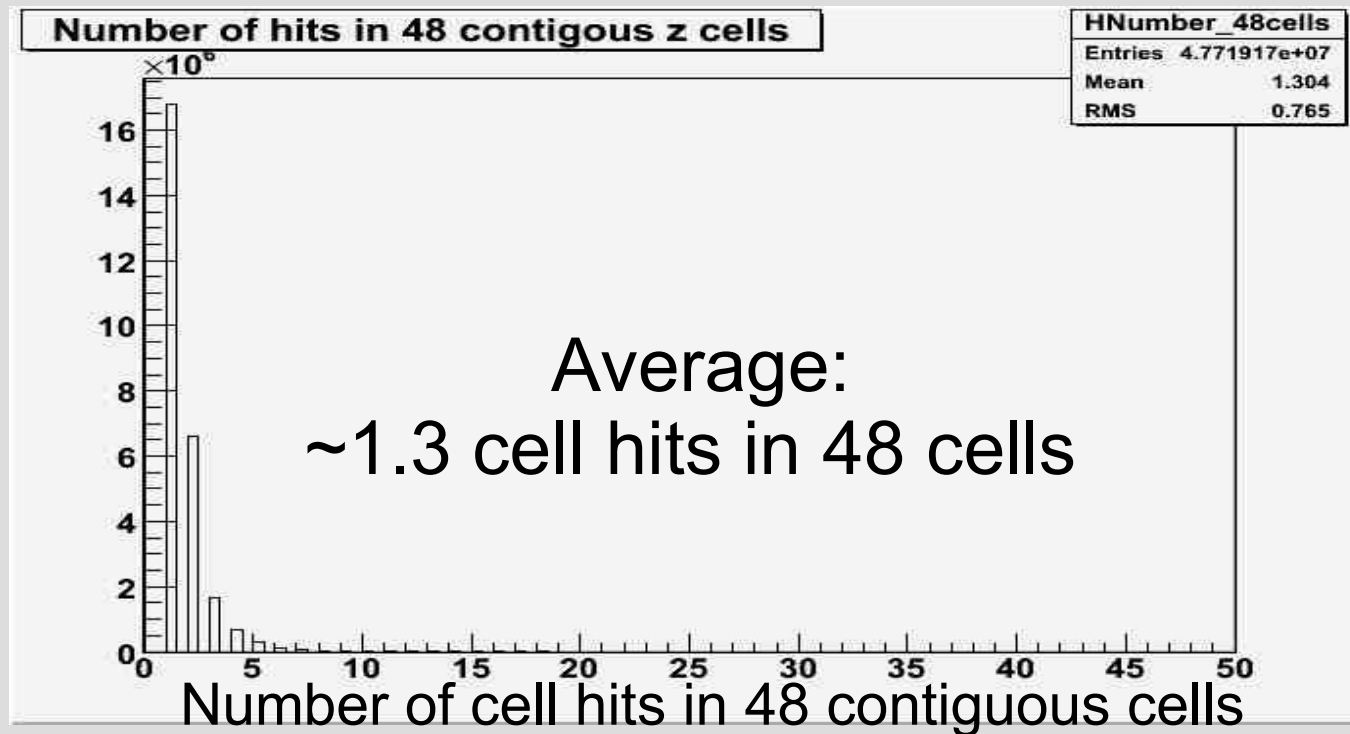
Future Prospects

- **Resolution studies**
- **Clustering algorithm development**
 - It can be developed only with shower topology.
(i.e. Each cell hit has identical energy.)
 - Sophisticated algorithm to save CPU time in this Tera pixel study.
- **Physics events studies**

Backup:

Readout by 48 contiguous cells (Under study as one option)

100GeV single e-
15 μ m Si sensitive thickness
50 μ m X 50 μ m cell size



Total energy also increased 30% compared with single cell.